

R-C Thermal Model Parameters

DESCRIPTION

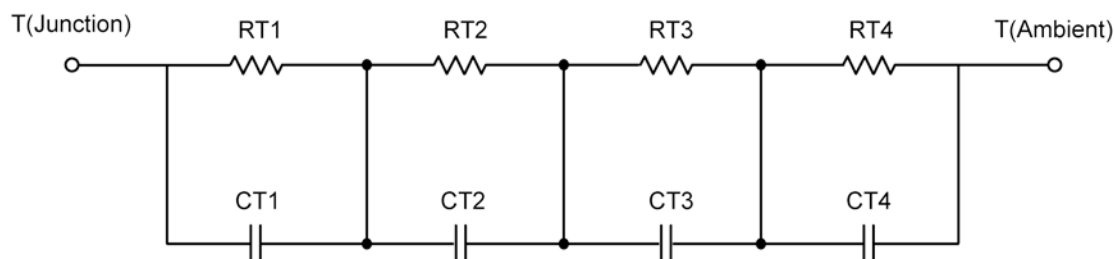
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

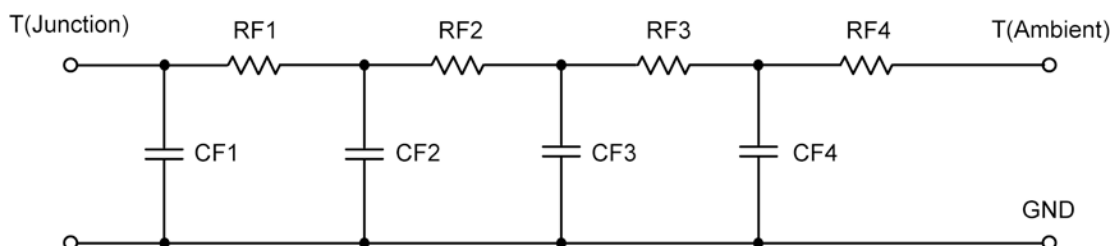
For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	27.0713	1.9818	N/A
RT2	13.9534	1.4707	N/A
RT3	14.8827	3.1117	N/A
RT4	49.0926	2.9358	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	5.0661 m	117.9294 u	N/A
CT2	260.9856 u	154.0489 u	N/A
CT3	391.3129 m	581.9782 u	N/A
CT4	2.2125	246.5084 u	N/A

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	14.3660	2.5823	N/A
RF2	27.3222	4.5152	N/A
RF3	18.7728	1.0943	N/A
RF4	44.5390	1.3082	N/A
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	221.9388 u	35.2139 u	N/A
CF2	4.4046 m	53.5437 u	N/A
CF3	315.7482 m	365.0170 u	N/A
CF4	2.0547	457.7854 u	N/A

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

